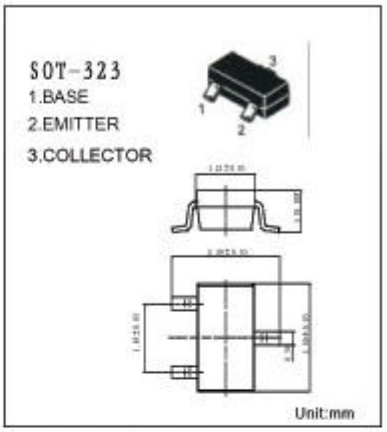
SOT-323 Plastic-Encapsulate Transistors

MMST3906 TRANSISTOR (PNP)



FEATURES

Power dissipation

P_{CM}: 0.2 W (Tamb=25℃)

Collector current

I_{CM} : -0.2 A

Collector-base voltage

$V_{(BR)\ CBO}$: -40 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C= -10 μA, I_E=0	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C= -1 mA, I_B=0	-40		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E= -10 μA, I_C=0	-5		V
Collector cut-off current	I_{CBO}	V_{CB}= -40 V, I_E=0		-0.1	μA
Collector cut-off current	I_{CEO}	V_{CE}= -40 V, I_B=0		-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= -5V, I_C=0		-0.1	μA
DC current gain	$h_{FE\ (1)}$	V_{CE}= -1V, I_C= -10mA	100	300	
	$h_{FE\ (2)}$	V_{CE}= -1V, I_C= -50mA	60		
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=-50 mA, I_B= -5mA		-0.3	V
Base-emitter saturation voltage	V_{BE}(sat)	I_C= -50 mA, I_B= -5mA		-0.95	V
Transition frequency	f_T	V_{CE}= -20V, I_C= -10mA f=100MHz	300		MHz
Output Capacitance	C_{ob}	V_{CB}=-5V, I_E= 0 f=1MHz		4.5	pF
Delay time	t_d	V_{CC}=-3V, I_C=-10mA		35	nS
Rise time	t_r	$V_{BE(off)}$=-0.5V, I_{B1}=-1mA		35	nS
Storage time	t_S	V_{CC}=-3V, I_C=-10mA		225	nS
Fall time	t_f	I_{B1}= I_{B2}= -1mA		75	nS

Marking: K5N